

IN THE SPECIFICATION:

Please replace paragraph number [0050] with the following rewritten paragraph:

[0050] Once CMP pad 20 has been conditioned in accordance with the method of the present-invention invention, abrasive particles 14 or other debris 46 are removed from CMP pad 20 by exposing at least polishing surface 22 of CMP pad 20 to chemical 80. Accordingly, conditioning system 60 includes a chemical source 70 that is configured to apply chemical 80 to CMP pad 20. Chemical source 70 may be of any type known in the art and include, for example, an applicator, such as a spray head or a roller, for applying chemical 80 to CMP pad 20, or a chemical bath into which CMP pad 20 may be at least partially disposed.